

FMI20N50E

FUJI POWER MOSFET

Super FAP-E³ series

N-CHANNEL SILICON POWER MOSFET

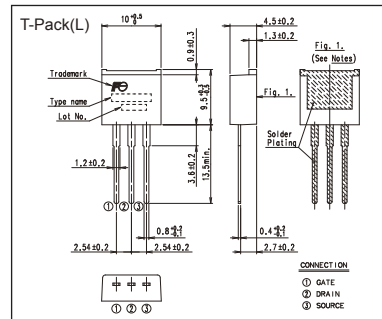
■ Features

- Maintains both low power loss and low noise
- Lower $R_{DS(on)}$ characteristic
- More controllable switching dV/dt by gate resistance
- Smaller V_{GS} ringing waveform during switching
- Narrow band of the gate threshold voltage ($3.0 \pm 0.5V$)
- High avalanche durability

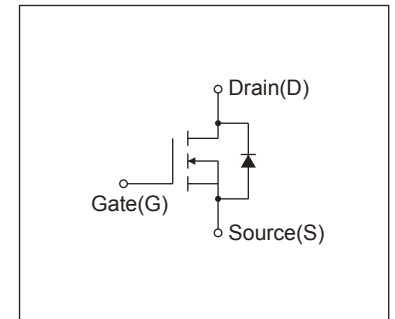
■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

■ Outline Drawings [mm]



■ Equivalent circuit schematic



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings at $T_c=25^\circ C$ (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V_{DS}	500	V	
	V_{DSX}	500	V	$V_{GS} = -30V$
Continuous Drain Current	I_D	± 20	A	
Pulsed Drain Current	I_{DP}	± 80	A	
Gate-Source Voltage	V_{GS}	± 30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I_{AR}	20	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E_{AS}	582.5	mJ	Note*2
Repetitive Maximum Avalanche Energy	E_{AR}	27	mJ	Note*3
Peak Diode Recovery dV/dt	dV/dt	7.4	kV/ μs	Note*4
Peak Diode Recovery $-di/dt$	$-di/dt$	100	A/ μs	Note*5
Maximum Power Dissipation	P_D	2.16	W	$T_a=25^\circ C$
		270		$T_c=25^\circ C$
Operating and Storage Temperature range	T_{ch}	150	$^\circ C$	
	T_{stg}	-55 to +150	$^\circ C$	

● Electrical Characteristics at $T_c=25^\circ C$ (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	500	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=500V, V_{GS}=0V$	-	-	25	μA
		$V_{DS}=400V, V_{GS}=0V$	-	-	250	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	10	100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$I_D=10A, V_{GS}=10V$	-	0.27	0.31	Ω
Forward Transconductance	g_{fs}	$I_D=10A, V_{DS}=25V$	11	22	-	S
Input Capacitance	C_{iss}	$V_{DS}=25V$	-	2650	3980	pF
Output Capacitance	C_{oss}	$V_{GS}=0V$	-	250	375	
Reverse Transfer Capacitance	C_{rss}	$f=1MHz$	-	19	28.5	
Turn-On Time	$t_{d(on)}$	$V_{cc}=300V$	-	22	33	ns
	t_r	$V_{GS}=10V$	-	11	16.5	
Turn-Off Time	$t_{d(off)}$	$I_D=10A$	-	120	180	
	t_f	$R_{GS}=10\Omega$	-	21	31.5	
Total Gate Charge	Q_G	$V_{cc}=250V$	-	77	115.5	nC
Gate-Source Charge	Q_{GS}	$I_D=20A$	-	17	25.5	
Gate-Drain Charge	Q_{GD}	$V_{GS}=10V$	-	22	33	
Avalanche Capability	I_{AV}	$L=1.07mH, T_{ch}=25^\circ C$	20	-	-	A
Diode Forward On-Voltage	V_{SD}	$I_F=20A, V_{GS}=0V, T_{ch}=25^\circ C$	-	0.90	1.35	V
Reverse Recovery Time	t_{rr}	$I_F=20A, V_{GS}=0V$	-	0.5	-	μs
Reverse Recovery Charge	Q_{rr}	$-di/dt=100A/\mu s, T_{ch}=25^\circ C$	-	7	-	μC

● Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	$R_{th(ch-c)}$	Channel to Case			0.460	$^\circ C/W$
	$R_{th(ch-a)}$	Channel to Ambient			62.0	$^\circ C/W$

Note *1 : $T_{ch} \leq 150^\circ C$

Note *2 : Stating $T_{ch}=25^\circ C, I_{AS}=8A, L=16.7mH, V_{cc}=50V, R_G=50\Omega$

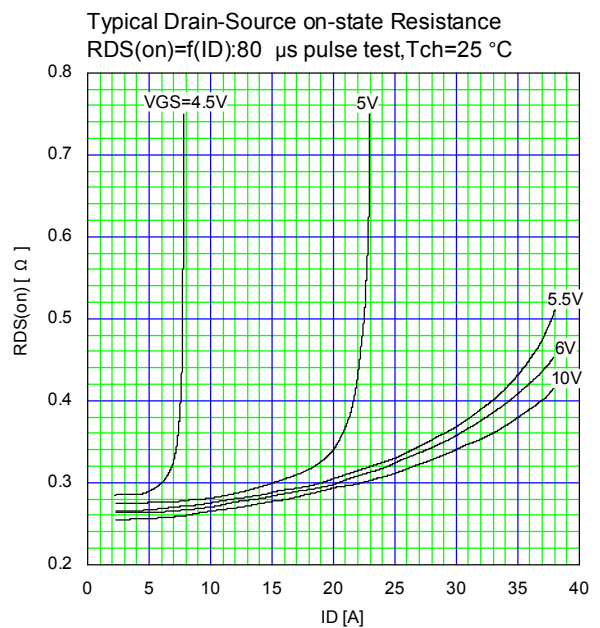
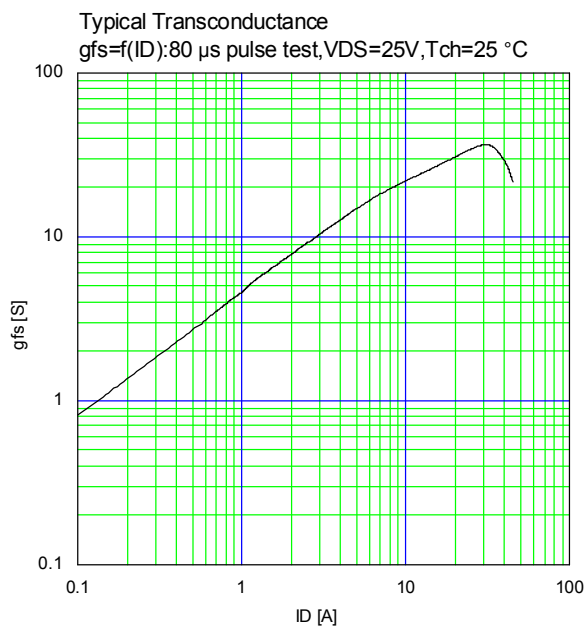
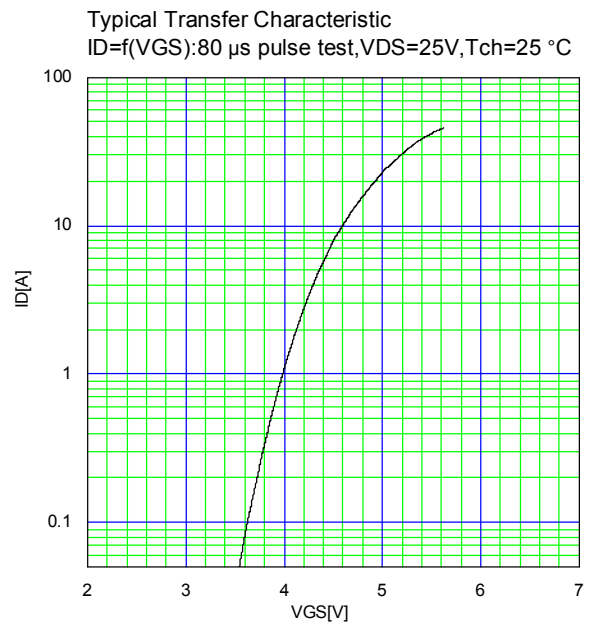
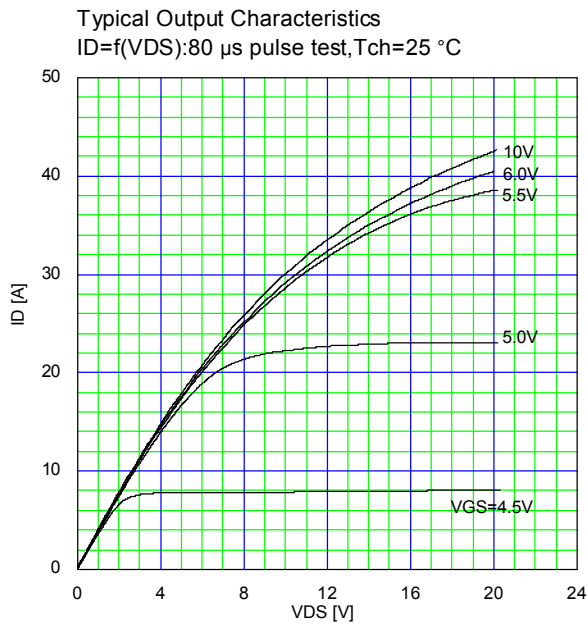
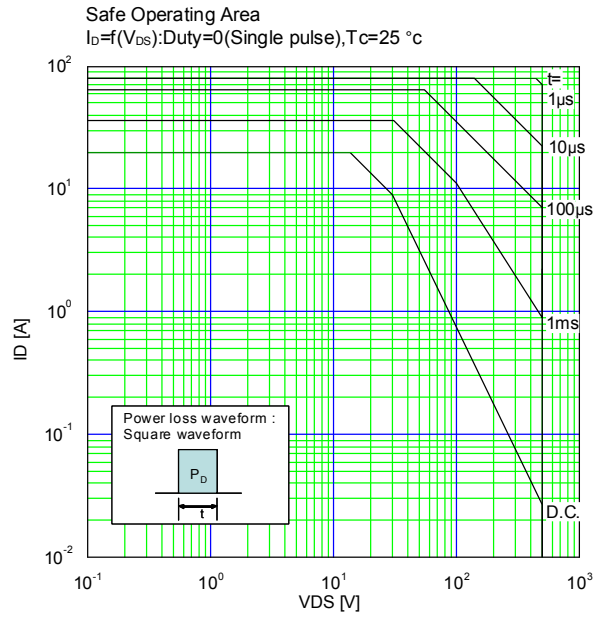
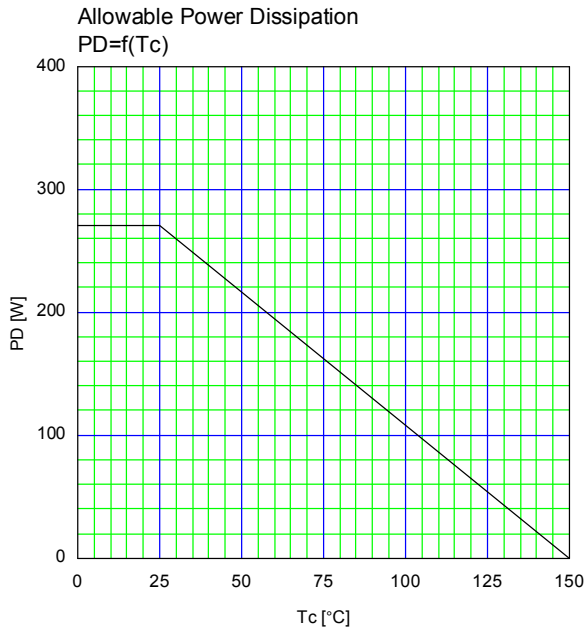
E_{AS} limited by maximum channel temperature and avalanche current.
See to 'Avalanche Energy' graph.

Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.

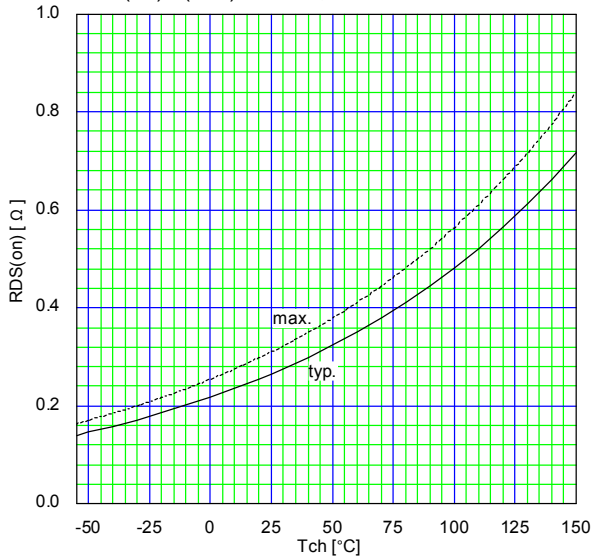
See to the 'Transient Thermal impedance' graph.

Note *4 : $I_F \leq I_D, -di/dt=100A/\mu s, V_{cc} \leq BV_{DSS}, T_{ch} \leq 150^\circ C$.

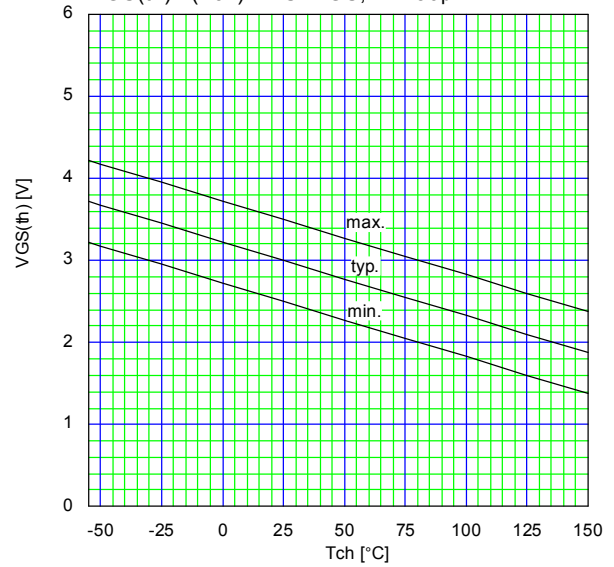
Note *5 : $I_F \leq I_D, dv/dt=7.4kV/\mu s, V_{cc} \leq BV_{DSS}, T_{ch} \leq 150^\circ C$.



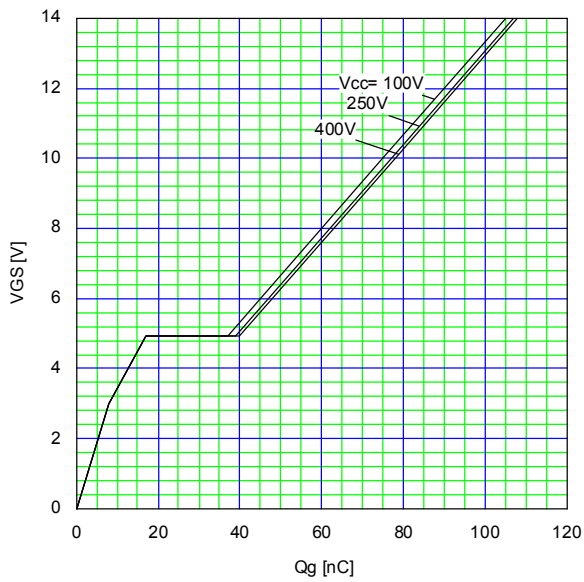
Drain-Source On-state Resistance
 $R_{DS(on)} = f(T_{ch}): I_D = 10A, V_{GS} = 10V$



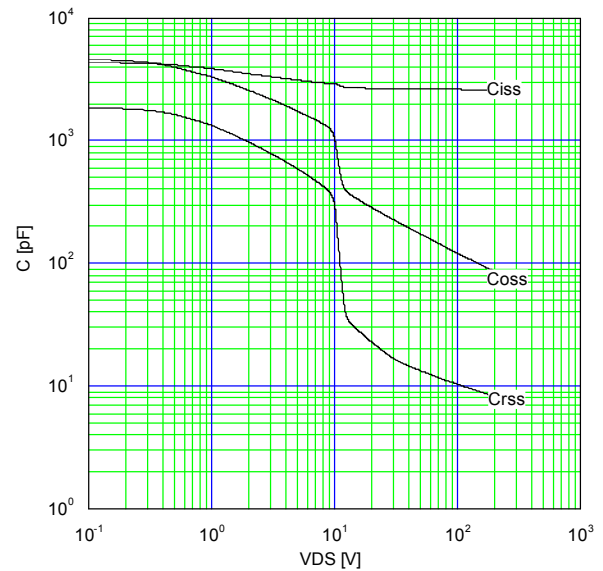
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)} = f(T_{ch}): V_{DS} = V_{GS}, I_D = 250\mu A$



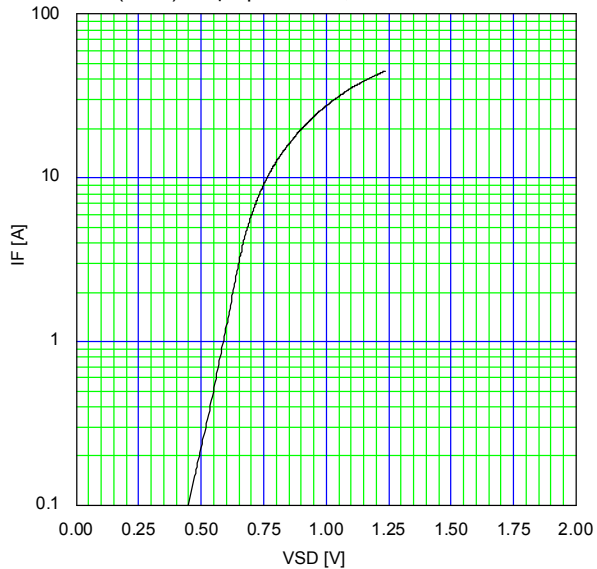
Typical Gate Charge Characteristics
 $V_{GS} = f(Q_g): I_D = 20A, T_{ch} = 25\text{ °C}$



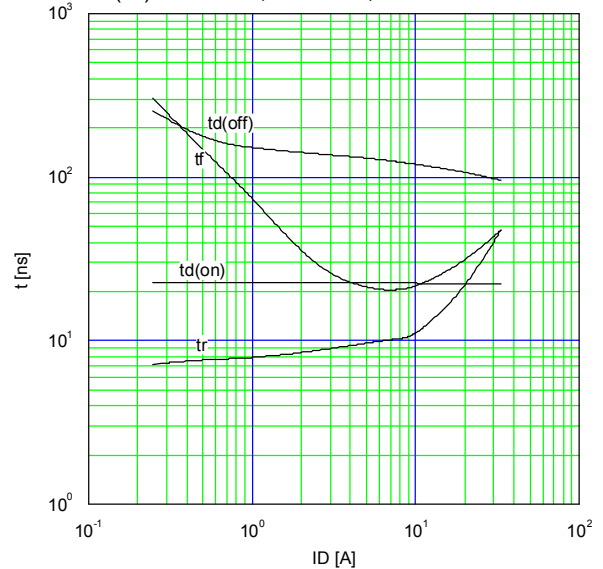
Typical Capacitance
 $C = f(V_{DS}): V_{GS} = 0V, f = 1MHz$

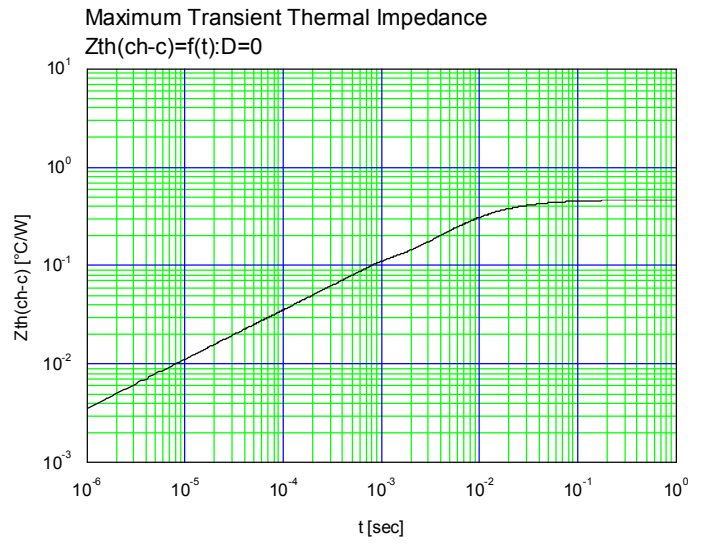
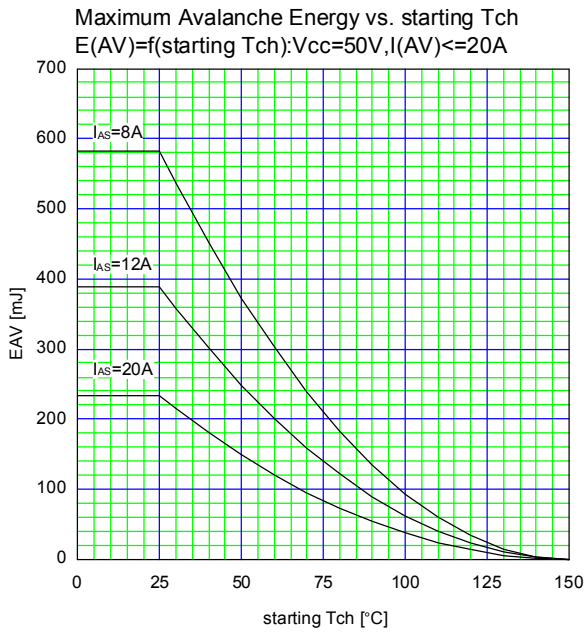


Typical Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD}): 80\ \mu s\ pulse\ test, T_{ch} = 25\text{ °C}$



Typical Switching Characteristics vs. I_D
 $t = f(I_D): V_{cc} = 300V, V_{GS} = 10V, R_G = 10\ \Omega$





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